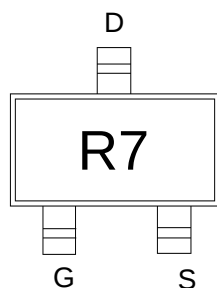


Features

- Trench Power LV MOSFET technology
- High density cell design for Low $R_{DS(ON)}$
- High Speed switching

Application

- Battery protection
- Load switch
- Power management

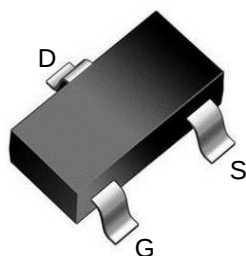


R7: Device code

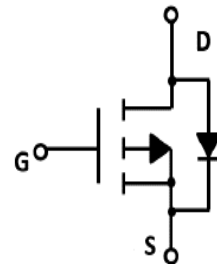
Marking and pin assignment

Product Summary

V_{DS}	$R_{DS(ON)}$ MAX	I_D MAX
-30V	60mΩ@-10V	-4.1A
	90mΩ@-4.5V	



SOT-23 top view



Schematic diagram



Pb-Free



RoHS



Halogen-Free

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Unit
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Common Ratings ($T_C=25^\circ\text{C}$ Unless Otherwise Noted)

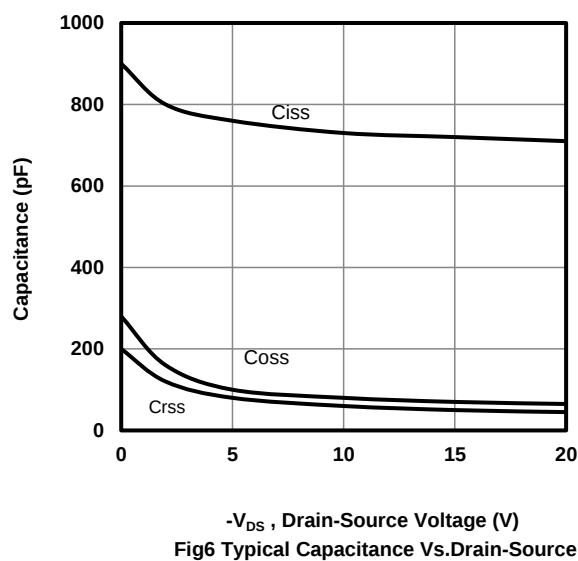
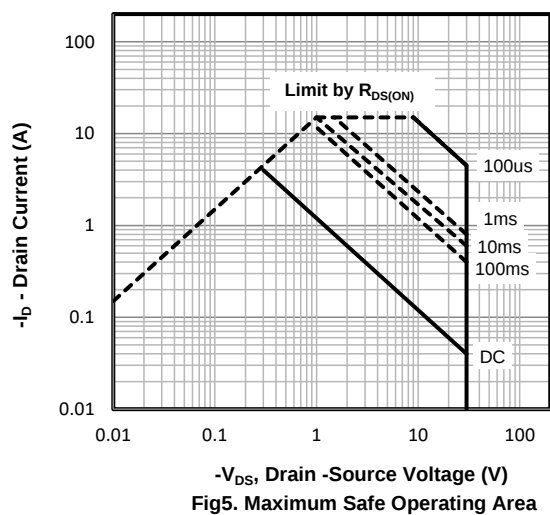
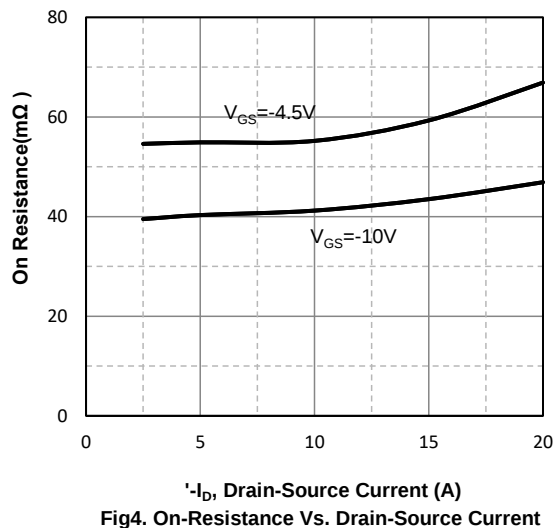
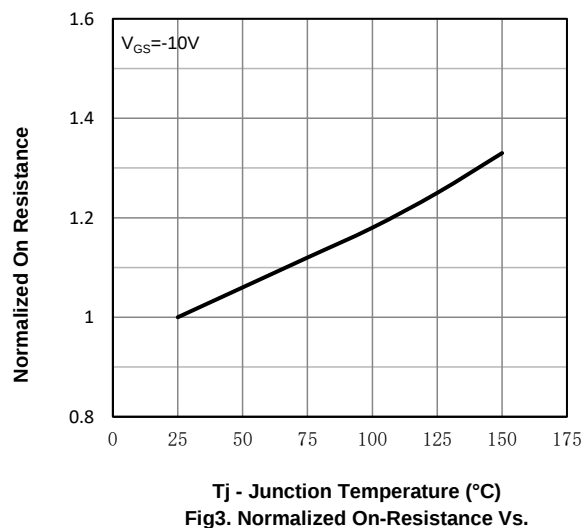
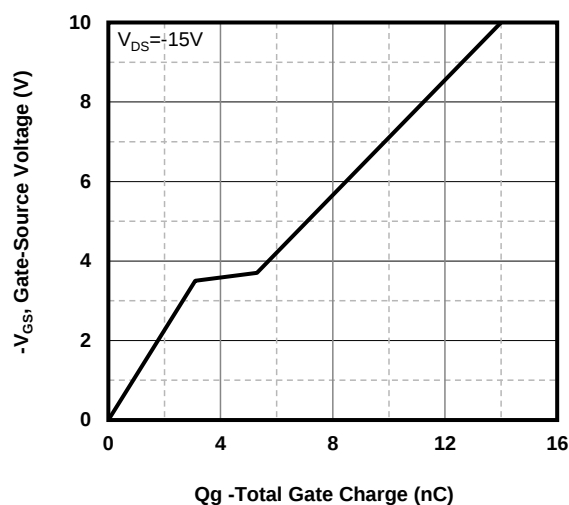
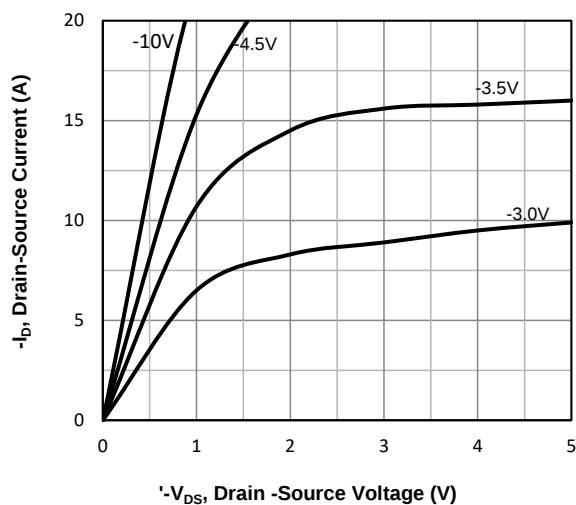
V_{DS}	Drain-Source Breakdown Voltage	-30	V
V_{GS}	Gate-Source Voltage	± 20	V
T_J	Maximum Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-50 to 155	$^\circ\text{C}$
I_S	Diode Continuous Forward Current	$T_C=25^\circ\text{C}$ -4.1	A

Mounted on Large Heat Sink

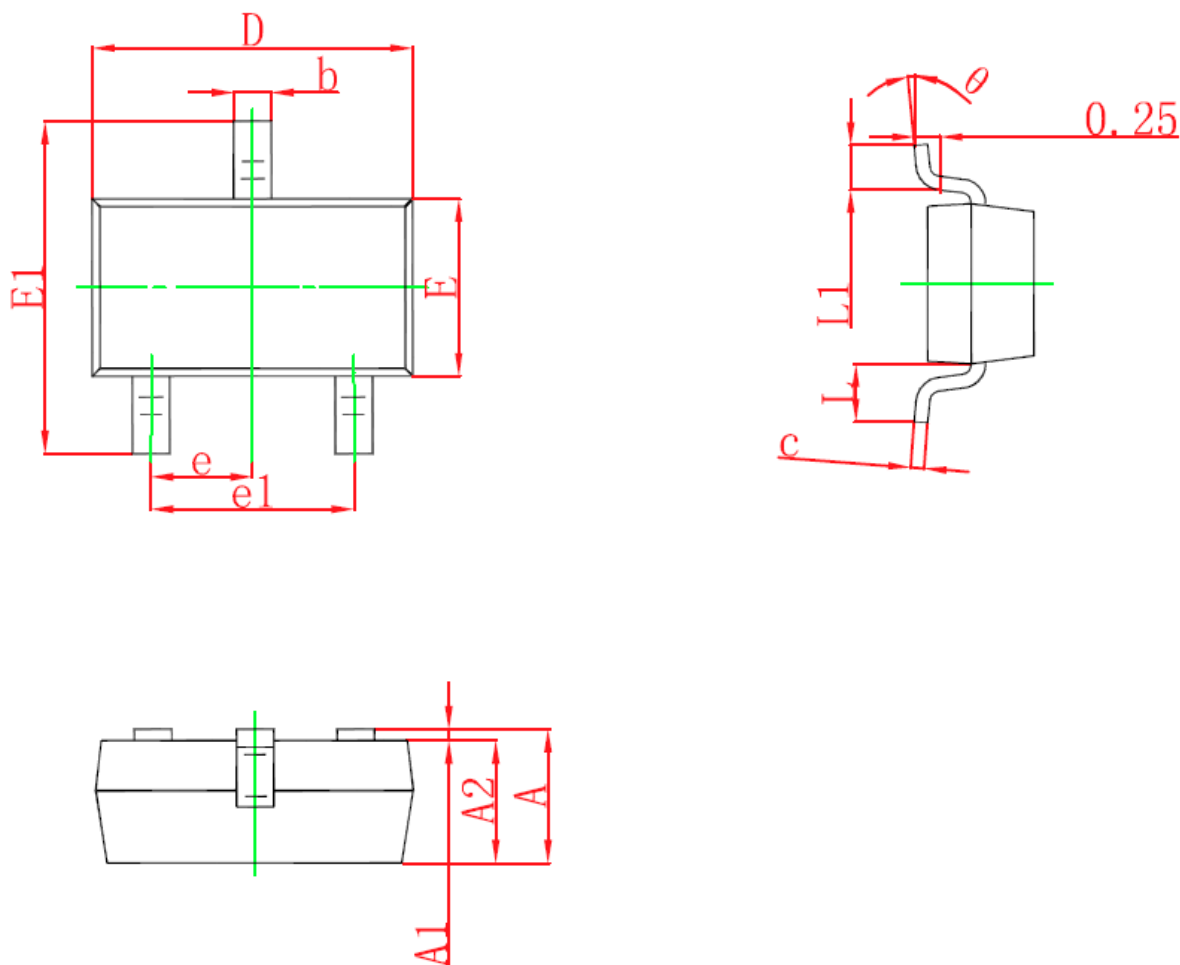
I_{DM}	Pulse Drain Current Tested	$T_C=25^\circ\text{C}$ -15	A
I_D	Continuous Drain Current	$T_C=25^\circ\text{C}$ -4.1	A
P_D	Maximum Power Dissipation	$T_C=25^\circ\text{C}$ 1.5	W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	82	$^\circ\text{C/W}$

Electrical Characteristics (TJ=25℃ unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-30	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-30V, V _{GS} =0V	--	--	-1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-1.0	-1.5	-2.5	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =-10V, I _D =-4.1A	--	40	60	mΩ
		V _{GS} =-4.5V, I _D =-3.5A	--	55	90	mΩ
Dynamic Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz	--	570	--	pF
C _{OSS}	Output Capacitance		--	80	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	70	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DS} =-15V, I _D =-4.2A, V _{GS} =-10V	--	11.5	--	nC
Q _{gs}	Gate Source Charge		--	2.3	--	nC
Q _{gd}	Gate Drain Charge		--	2.1	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DS} =-15V, I _D =-1A, V _{GS} =-10V, R _G =3Ω	--	3.8	--	nS
t _r	Turn-on Rise Time		--	17.5	--	nS
t _{d(off)}	Turn-Off Delay Time		--	18	--	nS
t _f	Turn-Off Fall Time		--	21.8	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	TJ=25℃, Is=-4A,	--	--	-1.2	V

Typical Operating Characteristics



SOT-23 Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E1	2.250	2.550	0.088	0.100
E	1.200	1.400	0.047	0.055
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°